

MITSUBISHI IGBT MODULES  
**CM200DY-24NF**

HIGH POWER SWITCHING USE

**CM200DY-24NF**



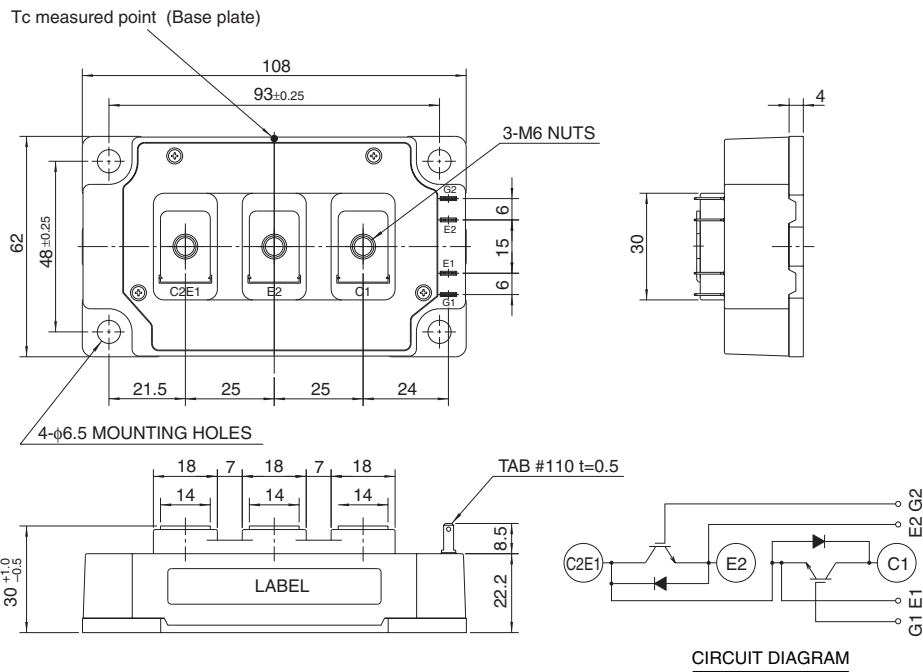
- IC .....200A
- VCES ..... 1200V
- Insulated Type
- 2-elements in a pack

**APPLICATION**

General purpose inverters & Servo controls, etc

**OUTLINE DRAWING & CIRCUIT DIAGRAM**

Dimensions in mm



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**MAXIMUM RATINGS (T<sub>J</sub> = 25°C, unless otherwise specified)**

Symbol	Parameter	Conditions	Ratings	Unit
V <sub>CE</sub> S	Collector-emitter voltage	G-E Short	1200	V
V <sub>GE</sub> S	Gate-emitter voltage	C-E Short	±20	V
I <sub>C</sub>	Collector current	DC, T <sub>C</sub> ' = 112°C <sup>*3</sup>	200	A
I <sub>CM</sub>		Pulse (Note 2)	400	A
I <sub>E</sub> (Note 1)	Emitter current		200	A
I <sub>EM</sub> (Note 1)		Pulse (Note 2)	400	A
P <sub>C</sub> (Note 3)	Maximum collector dissipation	T <sub>C</sub> = 25°C	1130	W
T <sub>J</sub>	Junction temperature		-40 ~ +150	°C
T <sub>stg</sub>	Storage temperature		-40 ~ +125	°C
V <sub>iso</sub>	Isolation voltage	Terminals to base plate, f = 60Hz, AC 1 minute	2500	V <sub>rms</sub>
—	Torque strength	Main terminals M6 screw	3.5 ~ 4.5	N • m
—		Mounting M6 screw	3.5 ~ 4.5	N • m
—	Weight	Typical value	400	g

**ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C, unless otherwise specified)**

Symbol	Parameter	Test conditions	Limits			Unit	
			Min.	Typ.	Max.		
I <sub>CES</sub>	Collector cutoff current	V <sub>CE</sub> = V <sub>CE</sub> S, V <sub>GE</sub> = 0V	—	—	1	mA	
V <sub>GE(th)</sub>	Gate-emitter threshold voltage	I <sub>C</sub> = 20mA, V <sub>CE</sub> = 10V	6	7	8	V	
I <sub>GES</sub>	Gate leakage current	±V <sub>GE</sub> = V <sub>GES</sub> , V <sub>CE</sub> = 0V	—	—	0.5	μA	
V <sub>CE(sat)</sub>	Collector-emitter saturation voltage	I <sub>C</sub> = 200A, V <sub>GE</sub> = 15V	T <sub>J</sub> = 25°C	—	1.8	2.5	V
			T <sub>J</sub> = 125°C	—	2.0	—	
C <sub>ies</sub>	Input capacitance	V <sub>CE</sub> = 10V V <sub>GE</sub> = 0V	—	—	47	nF	
C <sub>oes</sub>	Output capacitance		—	—	4	nF	
C <sub>res</sub>	Reverse transfer capacitance		—	—	0.9	nF	
Q <sub>G</sub>	Total gate charge	V <sub>CC</sub> = 600V, I <sub>C</sub> = 200A, V <sub>GE</sub> = 15V	—	1350	—	nC	
t <sub>d(on)</sub>	Turn-on delay time	V <sub>CC</sub> = 600V, I <sub>C</sub> = 200A V <sub>GE</sub> = ±15V R <sub>G</sub> = 1.6Ω, Inductive load I <sub>E</sub> = 200A	—	—	500	ns	
t <sub>r</sub>	Turn-on rise time		—	—	150	ns	
t <sub>d(off)</sub>	Turn-off delay time		—	—	600	ns	
t <sub>f</sub>	Turn-off fall time		—	—	350	ns	
t <sub>rr</sub> (Note 1)	Reverse recovery time		—	—	250	ns	
Q <sub>rr</sub> (Note 1)	Reverse recovery charge		—	7.5	—	μC	
V <sub>EC</sub> (Note 1)	Emitter-collector voltage	I <sub>E</sub> = 200A, V <sub>GE</sub> = 0V	—	—	3.2	V	
R <sub>th(j-c)Q</sub>	Thermal resistance <sup>*1</sup>	IGBT part (1/2 module)	—	—	0.11	K/W	
R <sub>th(j-c)R</sub>		FWDi part (1/2 module)	—	—	0.19	K/W	
R <sub>th(c-f)</sub>	Contact thermal resistance	Case to heat sink, Thermal compound Applied <sup>*2</sup> (1/2 module)	—	0.04	—	K/W	
R <sub>th(j-c')Q</sub>	Thermal resistance	Case temperature measured point is just under the chips	—	—	0.066 <sup>*3</sup>	K/W	
R <sub>G</sub>	External gate resistance		1.6	—	16	Ω	

\*1 : Case temperature (T<sub>C</sub>) measured point is shown in page OUTLINE DRAWING.

\*2 : Typical value is measured by using thermally conductive grease of λ = 0.9[W/(m • K)].

\*3 : Case temperature (T<sub>C</sub>) measured point is just under the chips.

If you use this value, R<sub>th(f-a)</sub> should be measured just under the chips.

Note 1. I<sub>E</sub>, V<sub>EC</sub>, t<sub>rr</sub> & Q<sub>rr</sub> represent characteristics of the anti-parallel, emitter-collector free-wheel diode (FWDi).

2. Pulse width and repetition rate should be such that the device junction temperature (T<sub>J</sub>) does not exceed T<sub>Jmax</sub> rating.

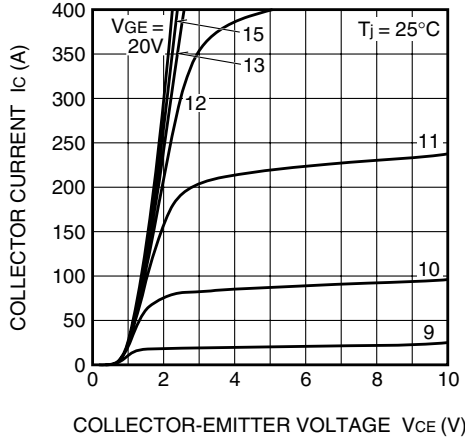
3. Junction temperature (T<sub>J</sub>) should not increase beyond 150°C.

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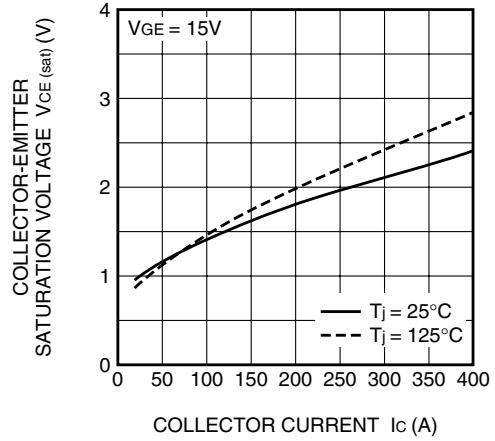
HIGH POWER SWITCHING USE

## PERFORMANCE CURVES

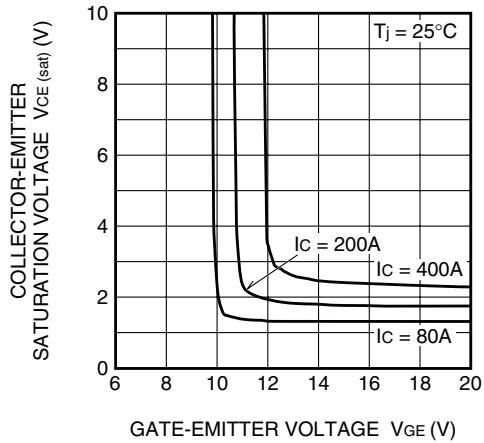
**OUTPUT CHARACTERISTICS (TYPICAL)**



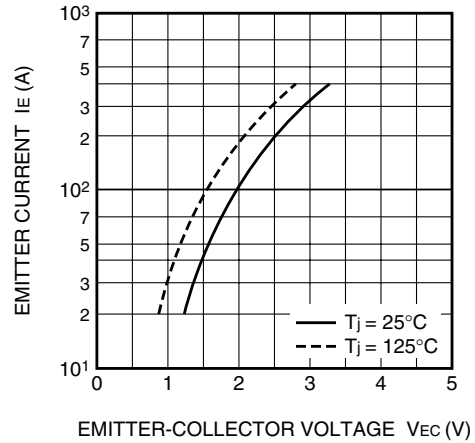
**COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)**



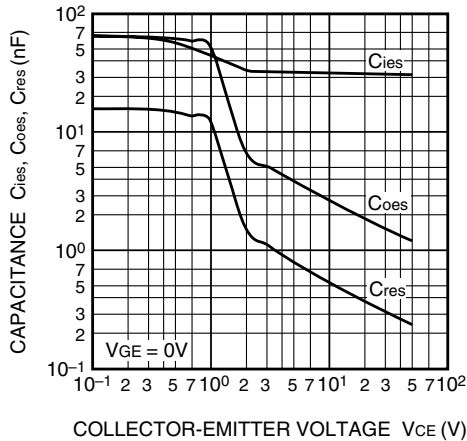
**COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)**



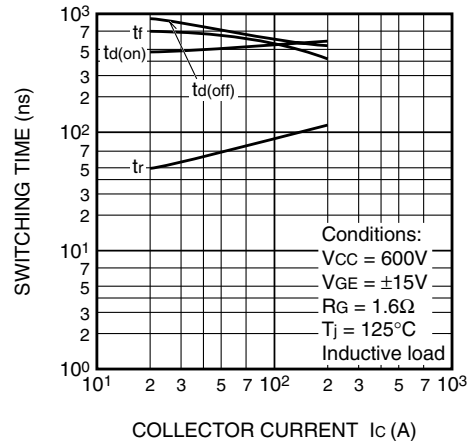
**FREE-WHEEL DIODE FORWARD CHARACTERISTICS (TYPICAL)**



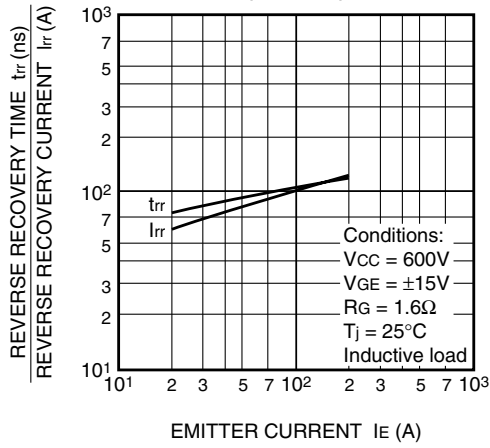
**CAPACITANCE-VCE CHARACTERISTICS (TYPICAL)**



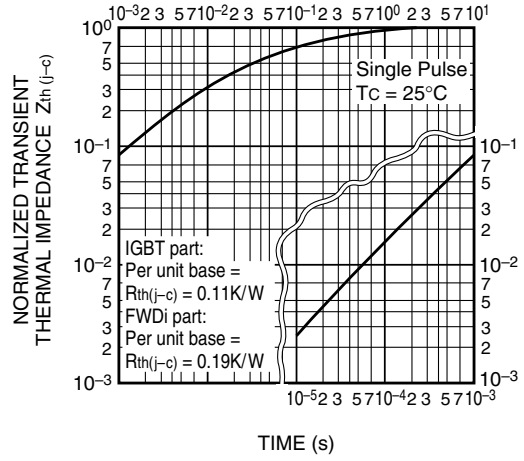
**HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)**



REVERSE RECOVERY CHARACTERISTICS OF FREE-WHEEL DIODE (TYPICAL)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (IGBT part & FWDi part)



GATE CHARGE CHARACTERISTICS (TYPICAL)

